

ABSTRACT

5 Provided is a copper alloy sputtering target containing 0.01 to (less than)
0.5wt% of at least 1 element selected from Al or Sn, and containing Mn or Si in a
total amount of 0.25wtppm or less. The above copper alloy sputtering target allows
the formation of a wiring material for a semiconductor element, in particular, a seed
layer being stable, uniform and free from the occurrence of coagulation during
electrolytic copper plating and exhibits excellent sputtering film formation
characteristics. A semiconductor element wiring formed with this target is also
10 provided.